

**SOT-363 Plastic-Encapsulate Transistors****MMBD4148TW /BAS16TW SWITCHING DIODE****FEATURES**

Power dissipation

 P_D : 200 mW ($T_{amb}=25^{\circ}C$)

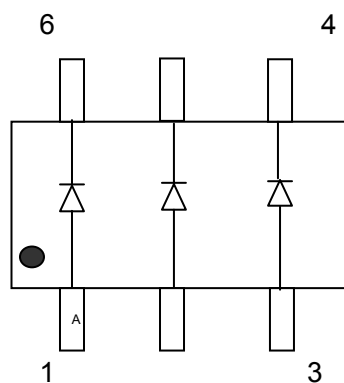
Collector current

 I_O : 150 mA

Collector-base voltage

 V_R : 75 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ **SOT-363**

MAKING: KA2

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=75V$ $V_R=20V$		1 0.025	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		0.715 0.855 1 1.25	V
Total capacitance	C_T	$V_R=0V, f=1MHz$		2	pF
Reveres recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	nS